

**RADIATION TOLERANT DTL**

These radiation-tolerant circuits are electrically similar to and functionally interchangeable with their Series 15930‡ counterparts. The terminal assignments are the same. They are mounted in the 14-pin H ceramic package and are intended for operation over the full military range of -55°C to 125°C.

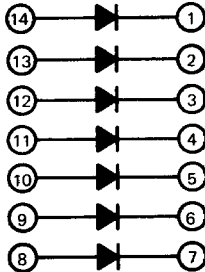
TYPE	FUNCTION
RSN15930 01	Expandable Dual 4-Input NAND Gate
RSN15932 02	Expandable Dual 4-Input NAND Buffer Gate
RSN15944 03	Expandable Dual 4-Input NAND Power Gate
RSN15945 04	J-K/R-S Flip-Flop
RSN15962 05	Triple 3-Input NAND Gate

**typical characteristics at 25°C free-air temperature**

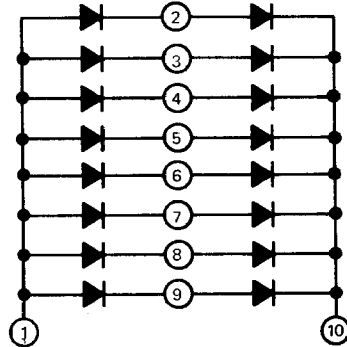
Propagation delay time	25 ns
Power dissipation	12 mW
D-c noise immunity	750 mV

**RADIATION TOLERANT DIODE ARRAYS**

RSN14925  
7-DIODE ARRAY  
14-PIN PACKAGE



RSN14097  
16-DIODE ARRAY  
10-PIN PACKAGE



**electrical characteristics at 25°C free-air temperature**

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>(BR)</sub> Reverse Breakdown Voltage	I <sub>R</sub> = 10 μA	40			V
I <sub>R</sub> Static Reverse Current	V <sub>R</sub> = 40 V			500	nA
V <sub>F</sub> Static Forward Voltage	I <sub>F</sub> = 500 mA			1.5	V
	I <sub>F</sub> = 100 mA	0.7		1	
C <sub>T</sub> Total Capacitance	V <sub>R</sub> = 0, f = 1 MHz		12		pF

† All radiation tolerant devices are supplied in H flat packages. See Section 1 for dimensional drawings.

‡ Refer to Section 11 for more complete data on Series 15930.

PRELIMINARY DATA:  
Supplementary data will be  
published at a later date.

**TEXAS INSTRUMENTS**  
INCORPORATED  
POST OFFICE BOX 5012 • DALLAS, TEXAS 75222

10